BT152-800R



SCR

Rev. 2 — 9 June 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated Silicon Controlled Rectifier in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

1.2 Features and benefits

- High thermal cycling performance
- High voltage capability

- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability

1.3 Applications

- Ignition circuits
- Motor control

- Protection circuits e.g. SMPS inrush current
- Voltage regulation

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
V_{RRM}	repetitive peak reverse voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see Figure 4; see Figure 5	-	-	200	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	-	-	220	Α
I _{T(AV)}	average on-state current	half sine wave; $T_{mb} \le 103 \text{ °C}$; see Figure 3	-	-	13	Α
I _{T(RMS)}	RMS on-state current	half sine wave; see Figure 1; see Figure 2	-	-	20	Α
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	3	32	mA



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		. 51
2	Α	anode	mb	A - X
3	G	gate		G sym037
mb	А	mounting base; connected to anode	1 2 3	
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

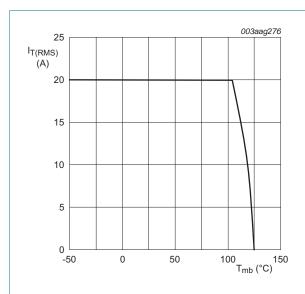
Type number	Package		
	Name	Description	Version
BT152-800R	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

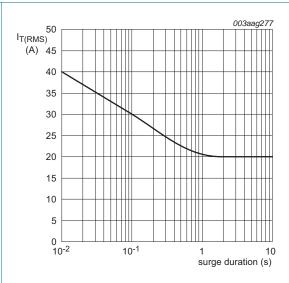
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	9	-	800	V
V_{RRM}	repetitive peak reverse voltage		-	800	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 103 °C; see <u>Figure 3</u>	-	13	Α
I _{T(RMS)}	RMS on-state current	half sine wave; see Figure 1; see Figure 2	-	20	Α
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; see Figure 4; see Figure 5	-	200	Α
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms	-	220	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	200	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 50 \text{ A}$; $I_G = 200 \text{ mA}$; $dI_G/dt = 200 \text{ mA/}\mu\text{s}$	-	200	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

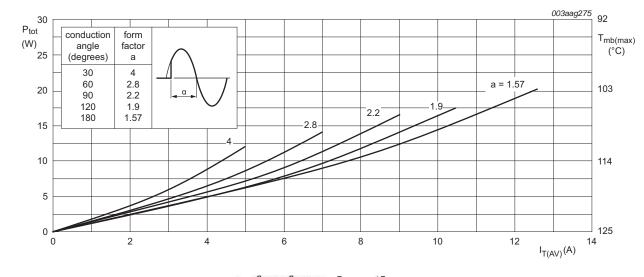




 $f = 50 \text{ Hz}; T_{mb} = 103 \text{ }^{\circ}\text{C}$

Fig 1. RMS on-state current as a function of mounting base temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values



 $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$

Fig 3. Total power dissipation as a function of average on-state current; maximum values

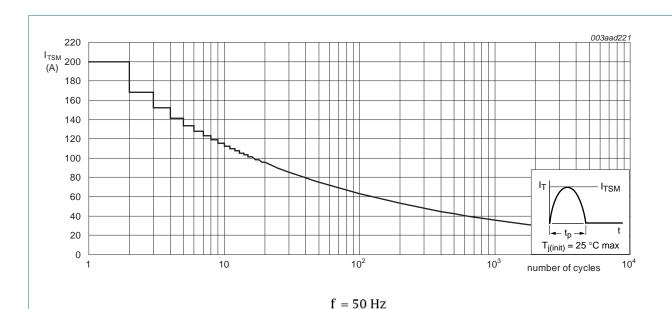
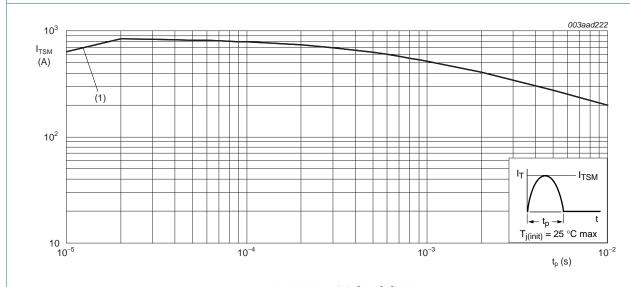


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



 $t_p \leq 10 \text{ ms}; \quad (1) dI_T/dt \text{ limit}$

Fig 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 6</u>	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

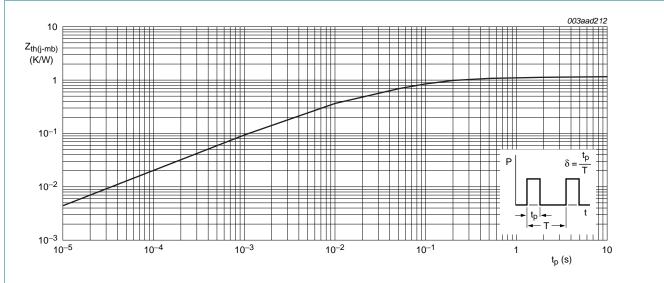


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

	Onaracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 7</u>	-	3	32	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	25	80	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	15	60	mA
V_{T}	on-state voltage	$I_T = 40 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{ c}}$	-	1.4	1.75	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.6	1.5	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.2	1	mA
I _R	reverse current	$T_j = 125 ^{\circ}C; V_R = 800 V$	-	0.2	1	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; exponential waveform; gate open circuit; see Figure 12	200	300	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 800 V; I_G = 100 mA; dI_G/dt = 5 A/ μ s	-	2	-	μs
tq	commutated turn-off time	$V_{DM} = 536 \text{ V}; T_j = 125 \text{ °C}; I_{TM} = 50 \text{ A}; V_R = 25 \text{ V}; (dI_T/dt)_M = 30 \text{ A/µs}; dV_D/dt = 50 \text{ V/µs}; R_{GK} = 100 \Omega$	-	70	-	μs

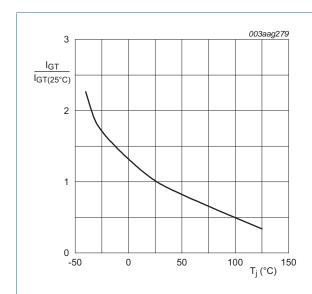


Fig 7. Normalized gate trigger current as a function of junction temperature

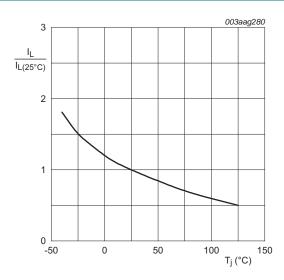
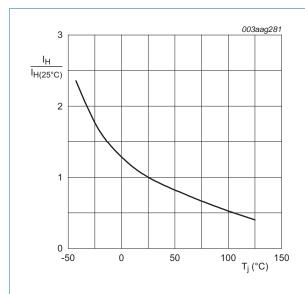


Fig 8. Normalized latching current as a function of junction temperature



Vo = 1.06 V; Rs = 0.03 Ω

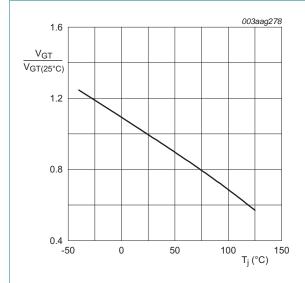
(1) Tj = 125 °C; typical values

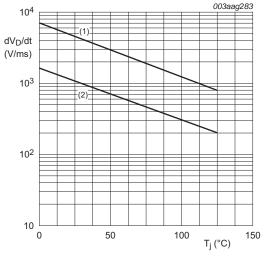
(2) Tj = 125 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature







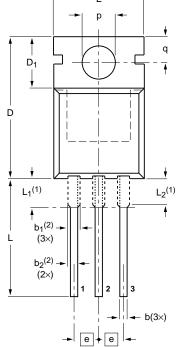
(1) $R_{GK} = 100 \Omega$ (2) Gate open circuit

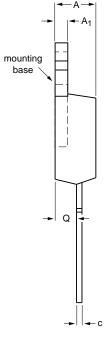
Fig 11. Normalized gate trigger voltage as a function of junction temperature

Fig 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78





0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 13. Package outline SOT78 (TO-220AB)

BT152-800R

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BT152-800R v.2	20110609	Product data sheet	-	BT152_SERIES v.1		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelin of NXP Semiconductors. 					
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.		
	 Type number 	BT152-800R separated from	data sheet BT152_SE	RIES v.1.		
BT152_SERIES v.1	19970301	Product specification	-	-		

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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